

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

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10. (Currently Amended): A semiconductor device having a plurality of semiconductor elements on a substrate, wherein some or all of the semiconductor elements each has a plurality of channel areas (a) which are formed in a semiconductor layer subjected to laser annealing respectively, and (b) which are the same conductive type channel areas, and the plurality of channel areas are electrically connected to each other and arranged separately and in different directions to each other and are connected in parallel to each other with respect to a current path.

11. (Original): The semiconductor device according to claim 10, wherein a distance between the plurality of channel areas is determined that a virtual channel width containing a separated space is larger than a width of a defectively processed area caused in the semiconductor layer during the laser annealing.

12. (Original): The semiconductor device according to claim 10, wherein the laser annealing is performed to polycrystallize an amorphous semiconductor layer in order to obtain a polycrystalline semiconductor layer.

13. (Previously Presented): A semiconductor device having a plurality of semiconductor elements on a substrate, wherein some or all of the semiconductor elements each has a plurality of channel areas which are formed in a semiconductor layer subjected to laser annealing respectively, and which are the same conductive type channel areas, and the plurality of channel areas are electrically connected to each other and arranged separately and in parallel to each other.

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cont.

14. (Previously Presented): The semiconductor device according to claim 13, wherein a distance between the plurality of channel areas is determined that a virtual channel width containing a separated space is larger than a width of a defectively processed area caused in the semiconductor layer during the laser annealing.

15. (Previously Presented): The semiconductor device according to claim 13, wherein the laser annealing is performed to polycrystallize an amorphous semiconductor layer in order to obtain a polycrystalline semiconductor layer.

16. (New): The semiconductor device according to claim 13, wherein the channel areas are connected in parallel with respect to a current path.
